10 Gbps Transimpedance Amplifier TA205C

PRODUCT DESCRIPTION

TA205C is a high gain transimpedance amplifier optimized for 10Gb/s fiber optic communication systems such as 10 Gigabit Ethernet, SONET OC-192 and SDH STM-64. Compared to TA205B, TA205C operates across a wider temperature range. The transimpedance amplifier consists mainly of a transimpedance stage, a differential gain stage, and a differential 50 Ω output driver. An internal DC-control circuit is included to maintain proper data crossover points. Due to high gain of the amplifier, a differential output of 100mVp-p or larger is available with input current larger than 10uAp-p, eliminating the need of a separate post-amplifier in most applications. The amplifier is available in die form and can be integrated with PIN or APD photodetector to function as an optical receiver in 10 Gbps systems.

KEY FEATURES

- $10 \text{ k}\Omega (80 \text{ dB}\Omega)$ differential transimpedance gain
- 9 GHz Bandwidth
- Typical noise current density: 10 pA/rt Hz
- Internal circuitry for maintaining data crossover points
- <30 kHz low cutoff frequency
- Input bias: +2.6 V
- Current consumption: 48 mA
- Power supply: +5.0 V
- Die size: 1.4 mm x 1.1 mm

BLOCK DIAGRAM



ELECTRICAL SPECIFICATIONS

Parameter	Symbol	Min	Typical	Max	Unit
Ambient Temperature	T_o	-40	25	85	°C
Differential Transimpedance	Z_t	7,000	10,000	12,000	Ω
Input Noise Current Density ¹	Inoise		10		pA/rtHz
Upper -3dB Bandwidth	BW	8	9	10	GHz
Low Frequency -3dB Cutoff ⁴	BW_{LF}	10	30	100	kHz
Maximum Output Swing ²	Vout	250	300	350	$\mathrm{mV}_{\mathrm{pp}}$
Group Delay Variation ¹	ΔGD		30		ps
Input Overload Current ³	I _{OL}		2		mA
Output Impedance	Z _{OUT}	45	50	55	Ω
Minimum Output Return Loss ¹	RL		10		dB
Current Consumption	I_{PS}	42	48	55	mA

Photodiode and bond wire reference model C_{pd}=0.2 pF and L_{pd}=0.7 nH

¹ 50 MHz to 10 GHz ² single-ended ³ for BER=1x10⁻¹²; 2³¹-1 PRBS @ 10Gb/s ⁴ 560pF external capacitor to pads Vsvo & Vref

PAD DESCRIPTION

Name	Function	I/O	Signal
VCCI	Power supply (input), +5.0 V	PS	DC
VCC	Power supply, +5.0 V	PS	DC
GND	Ground	GND	DC
IN	RF input, connected to anode of photodiode	Ι	RF
OUTP	Non-inverted Output	0	RF
OUTN	Inverted Output	0	RF
VSVO	Reference voltage output	0	DC
VREF	Reference voltage input	Ι	DC
VPD	Photodiode bias voltage	PS	DC
FIL	Filter resistor output, connected to cathode of photodiode	0	DC

BOND PAD ARRANGEMENTS

- Die Size: 1390±30 μm x 1090±30 μm
- Die thickness: 7mil



TYPICAL PERFORMANCE



Typical transimpedance gain with reference PD and bond wire



Typical 10Gb/s single-ended output of PIN-TA205C (Pin=-14dBm)

APPLICATION

To set the reference voltage (Vref) automatically and ensure proper low cutoff frequency, an external capacitor of 560pF or larger is recommended. A reference voltage is established through the servo circuitry in a feedback loop to maintain proper output DC offset voltage and data crossover points. Due to high internal gain of the amplifier, robust ground/power supplies, bond wire control, and electrical isolation between input and output ports of the die are all of paramount importance to prevent signal degradation or even oscillation. Please consult Euvis technical support for related issues.



BONDING REFERENCE

Bond wire inductance of 700pH is recommended for photodiode to TIA input connection; 300pH or less each of inductance is recommended for other bond wires.



Ordering Information:

E-mail: <u>sales@euvis.com</u> Tel: (805) 583-9888 Fax: (805) 583-9889

The information contained in this document is based on preliminary product test results. Characteristic data and other specifications are subject to change without notice. Customers are advised to confirm information in this advanced datasheet prior to using this information or placing the order.

Euvis Inc. does not assume any liability arising from the application or use of any product or circuit described herein, neither does it convey any license under its patents or any other rights.